



SEMICONDUCTOR

SR120 THRU SR1200

SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts

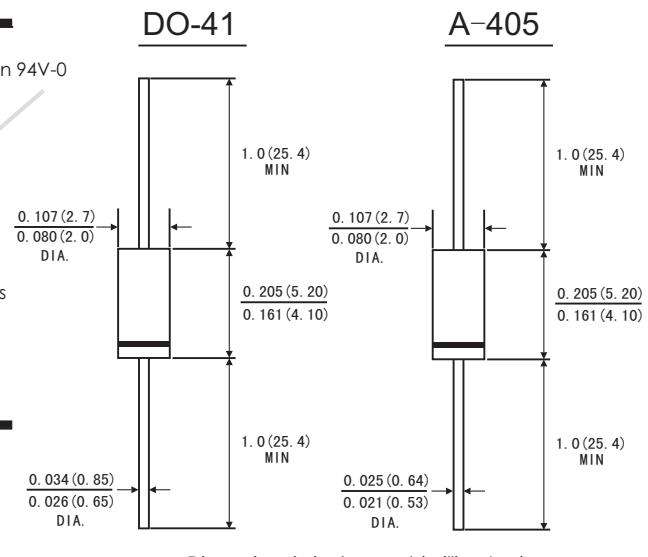
Forward Current - 1.0Ampere

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction, majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss, high efficiency
- High current capability, Low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2011/65/EU

MECHANICAL DATA

- Case: JEDEC DO-41/A-405 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, resistive or inductive load. For capacitive load, derate by 20%.)

	Symbols	SR 120	SR 130	SR 140	SR 160	SR 1100	SR 1150	SR 1200	Units			
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	60	100	150	200	Volts			
Maximum RMS voltage	V _{RMS}	14	21	28	42	71	105	140	Volts			
Maximum DC blocking voltage	V _{DC}	20	30	40	60	100	150	200	Volts			
Maximum average forward rectified current 0.375"(9.5mm) lead length (see Fig. 1)	I _(AV)	1.0						Amp				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	40.0						Amps				
Maximum instantaneous forward voltage at 1.0 A (Note 1)	V _F	0.55		0.70	0.85	0.90	0.95	Volts				
Maximum instantaneous reverse current at rated DC blocking voltage (Note 1)	T _A =25°C	100			20			μA				
	T _A =100°C	5			-			mA				
	T _A =125°C	-			3							
Typical junction capacitance (Note 3)	C _J	110						pF				
Typical thermal resistance (Note 2)	R _{θJA} R _{θJL}	50.0 15.0						°C/W				
Operating junction temperature range	T _J	-55 to +150						°C				
Storage temperature range	T _{STG}	-55 to +150						°C				

Notes: 1. Pulse test: 300μs pulse width, 1% duty cycle

2. Thermal resistance (from junction to ambient) Vertical P.C.B. mounted, with 1.5 X 1.5" (38X38mm) copper pads

3. Measured at 1.0MHz and reverse voltage of 4.0 volts

RATINGS AND CHARACTERISTIC CURVES SR120 THRU SR1200

FIG.1-FORWARD CURRENT DERATING CURVE

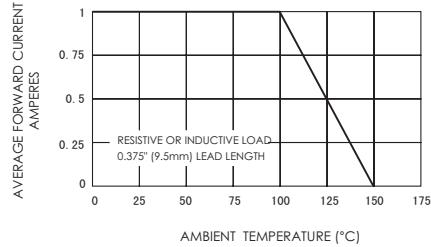


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

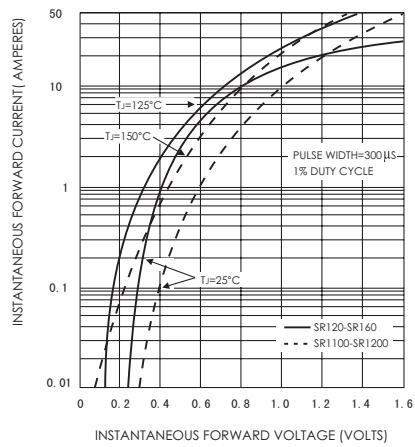


FIG.5-TYPICAL JUNCTION CAPACITANCE

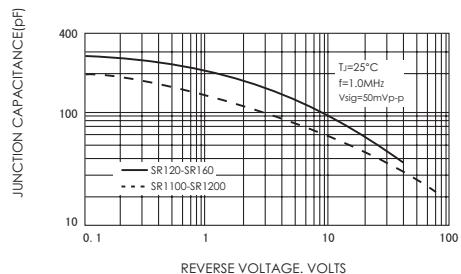


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

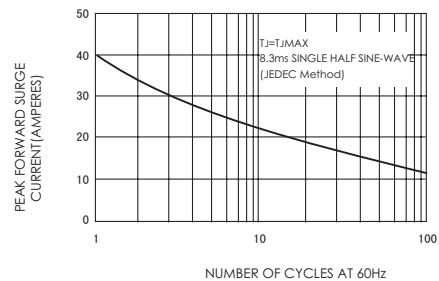


FIG.4-TYPICAL REVERSE CHARACTERISTICS

